GE MOBILE RADIO

MASTR®

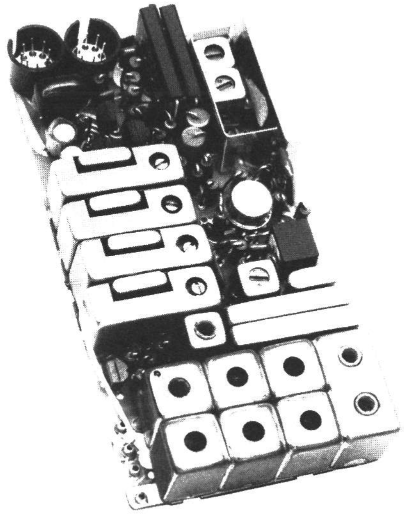
MVP Personal

150.8-174 MHz, RECEIVER TYPE ER-71-A

Maintenance Manual LBI-4888 B

DATAFILE FOLDER - DF-1111

ER-71-A



SPECIFICATIONS *

Audio Output (EIA)	500 milliwatts at less than 5% distortion	
Channel Spacing	30 kHz	
Sensitivity		
12 dB SINAD (EIA Method)	0.25 µV	
20 dB Quieting Method	0.35 µV	
Selectivity		
EIA Two-Signal	-75 dB at ±30 kHz	
20 dB Quieting Method	-110 dB at ±30 kHz	
Spurious Response	-70 dB	
Intermodulation (EIA)	-60 dB	
Audio Response	Within +2 and -10 dB of a standard 6 dB per octave de-emphasis curve from 300 to 3000 Hz (1000 Hz reference)	
Modulation Acceptance	±7.0 kHz	
Squelch Sensitivity		
Critical Squelch	0.15 µV	
Maximum Squelch	Greater than 20 dB Quieting	
Maximum Frequency Spacing	Full Performance	1dB Degradation In Sensitivity
	0.60 MHz	1.20 MHz

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

GENERAL ELECTRIC

TABLE OF CONTENTS

ILLUSTRATIONS

WARNING

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

General Electric MVP Personal Receiver Type ER-71-A, is a one through six-frequency, dual conversion FM receiver for operation in the 150.8 MHz to 174 MHz range. The receiver is constructed on a single printed wire board and utilizes both discrete components and Integrated Circuit Modules.

References to symbol numbers mentioned in the following text are found on the Schematic Diagram, Outline Diagram and Parts List (see Table of Contents). The typical circuit diagrams used in the text are representative of the circuits used in the Integrated Circuit Modules. A block diagram of the receiver is shown in Figure 1.

Supply voltage for the receiver includes a continuous 7.5 Volts for the squelch module, and a switched 7.5 Volts for the remaining receiver stages.

CIRCUIT ANALYSIS

OSCILLATOR MODULE

Oscillator Model 4EG36A10 (150.8-174 MHz) is a crystal-controlled Colpitts oscillator (see Figure 2). The entire oscillator is contained in a metal can with the receiver operating frequency printed on the top. The crystal frequency ranges from 14.533 to 17.11 MHz, and the crystal frequency is multiplied 9 times.

In multi-frequency receivers, additional oscillator modules are mounted on the receiver board. The single-frequency supply jumper is removed, and the proper frequency is selected by connecting the 5.4 Volts to the selected oscillator module through frequency selector switch S1 on the control unit.

Complete instructions for multi-frequency modifications are contained in the Multi-Frequency Modification Diagram (Refer to LBI-4902).

NOTE

All oscillator modules are individually compensated at the factory and cannot be repaired in the field. Any attempt to remove the oscillator cover will void the warranty.

BUFFER/TRIPLER

RF from the oscillator module is coupled to the base of Buffer/Tripler transistor Q301. Q301 prevents loading of the oscillator modules by the receiver Front End. L2 in the multiplier circuit of the receiver Front End, is part of the collector circuit of Q301 and is tuned to three times the oscillator frequency. Three times the oscillator frequency is metered at Multi-Test Point (TP5) on the receiver board.

RECEIVER FRONT END

The receiver Front End consists of three tuned helical resonators, an RF amplifier stage, a mixer stage and a multiplier circuit. RF from the antenna is coupled to a tap on L6. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to the third coil L8 through openings in the sides of the cans. RF is then coupled from a tap on L8 through C1 to the base of RF amplifier transistor Q1. The output of Q1 is developed across tuned circuit C2 and L1, and is applied to the base of the mixer transistor Q2 to be beat against the low-side injection frequency from the Multiplier Circuit.

The output of L2 in the multiplier circuit is applied to the anode of multiplier diode CR1. The two helical resonators following CR1 are tuned to three times the first multiplier frequency for a total multiplication of 9 times. The output of the helical resonators is direct-coupled to the emitter of the mixer transistor Q2. With the RF signal from the RF amplifier applied to the base of mixer Q2 and the low side injection frequency from the multiplier circuit applied to the emitter, the resultant 20-MHz IF frequency is coupled through the mixer collector tuned circuit (L2 & C6) to Crystal Filter FL301.

CRYSTAL FILTER

Crystal Filter FL301 follows the receive Front End mixer stage and provides a minimum of 40 dB stop-band attenuation at 20 MHz. The output of FL301 is coupled through L302 to 2nd Mixer and Oscillator Module U301-1.

2ND MIXER AND OSCILLATOR

The 20 megahertz signal coupled to the 2nd Mixer and Oscillator Module U301-1 is coupled to the base of 2nd Mixer transistor Q2. Also coupled to the base of Q2 is a 19.545 megahertz low side injection frequency from Colpitts oscillator Q1. The 20 megahertz High-IF signal and 19.545 megahertz low side injection frequency, produce a 455 kilohertz Low-IF output at U301-4. A typical 2nd mixer and oscillator circuit is shown in Figure 3.

The 455 Kilohertz Low-IF from 2nd Mixer and Oscillator Module U301-4 is coupled through Low-IF Filter L301 and Low-IF Ceramic Filter FL302. L301 and FL302 provide additional selectivity for the receiver.

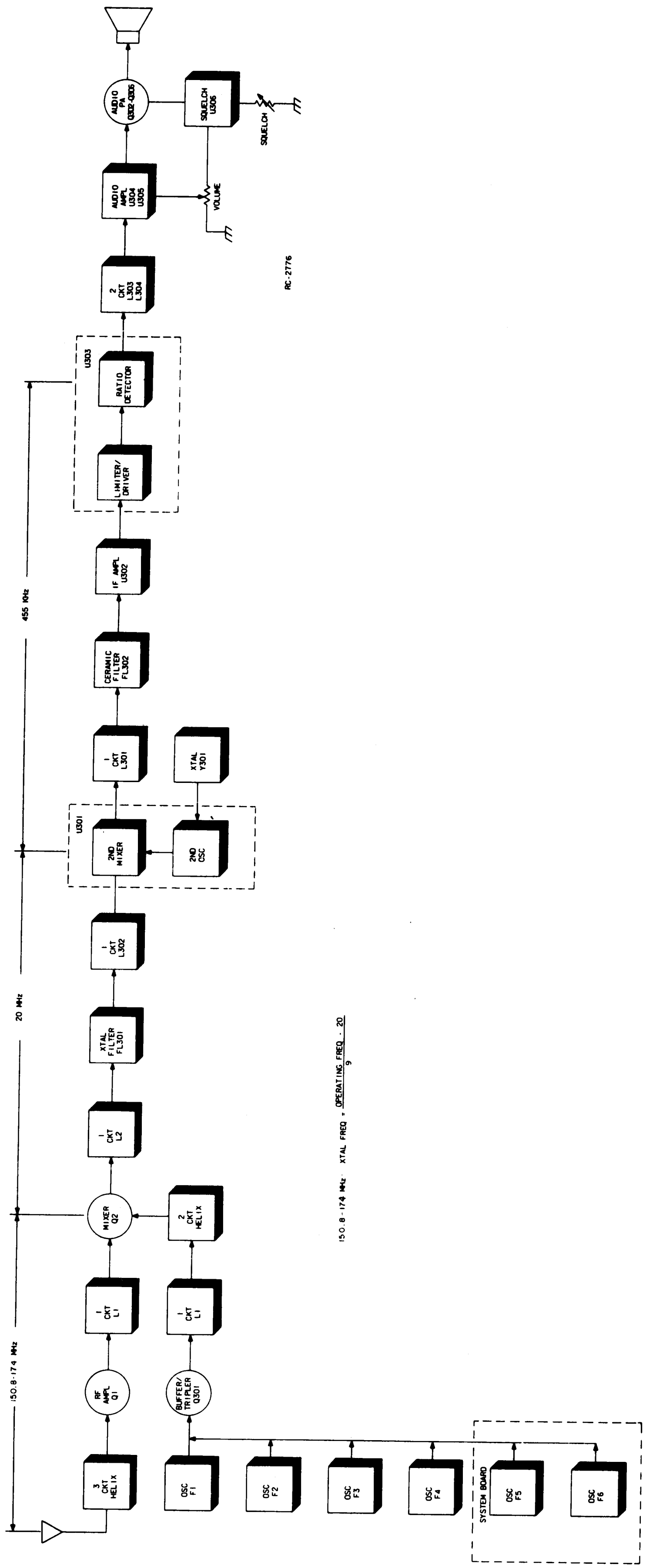


Figure 1 - Receiver Block Diagram

The output from L301 and FL302 is metered at TP4 and coupled to Low-IF Amplifier U302-6.

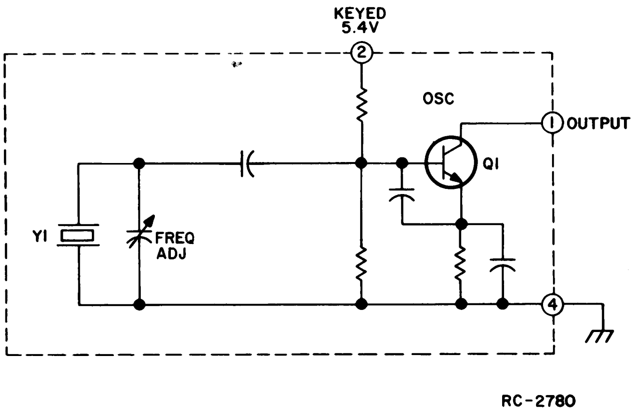


Figure 2 - Typical Oscillator Circuit

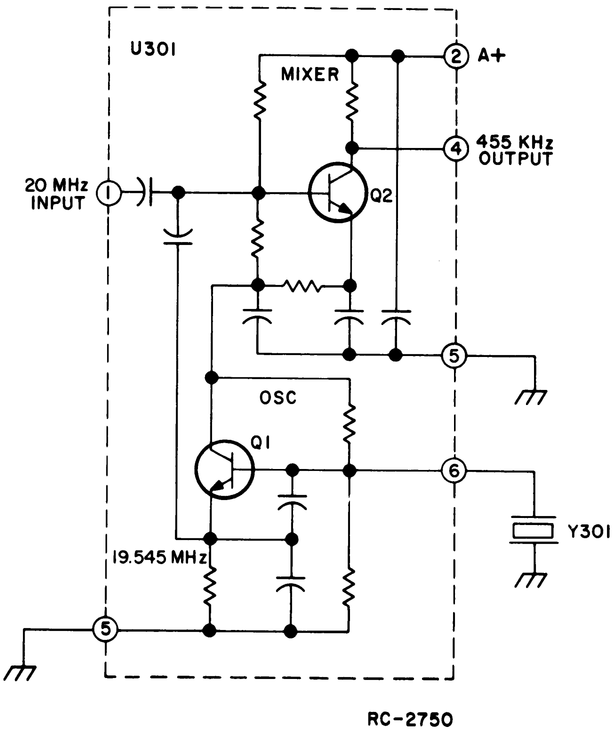


Figure 3 - Typical 2nd Mixer and Oscillator Circuit

IF AMPLIFIER

The 455 kilohertz Low-IF coupled to IF Amplifier U302-6 is applied to the base of amplifier Q1. A typical IF-amplifier circuit is shown in Figure 4. Further amplification is obtained through Q2 and Q3. The output of Q3 is applied to U302-1.

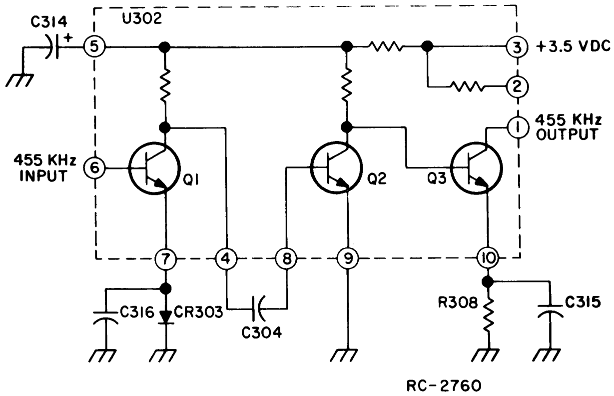


Figure 4 - Typical IF Amplifier Circuit

DRIVER/LIMITER AND RATIO DETECTOR

The 455 kilohertz Low-If Amplifier U302-1 is connected to Driver/Limiter and Ratio Detector Module U303-1. Typical Driver/Limiter and Ratio Detector Circuit is shown in Figure 5. The Low-IF is applied to the base of Driver/Limiter transistor Q1. The output of Q1 is connected to U303-6 and applied directly to the Ratio Detector Circuit through L303 and L304. Diodes CR1 and CR2 rectify the Low-IF and voltages, the sum of which always remain constant, develop across R1 and R2. Audio is developed as a result of the varying ratio of the voltages across R1 and R2. C1 stabilizes the circuit and keeps the sum of the voltages across R1 and R2 constant. The recovered audio is coupled from U303-9 through low pass filter R326 and C308 to Audio Amplifier Module U304/U305-1.

AUDIO AMPLIFIER

Audio and noise from Ratio Detector U303 is applied to Audio Amplifier module U304/U305-1. (U305 in Channel Guard applications). A typical audio amplifier circuit is shown in Figure 6.

Audio and noise is applied to the base of Q1. This stage operates as an emitter-follower for matching the impedance of the ratio detector to amplifier transistor Q2 and VOLUME control R701. The output of Q1 connects from Pin 2 to the base of amplifier Q2 (Pin 4) through the VOLUME control. The output of Q1 is also applied to the input of Squelch module U306.

Following amplifier Q2 is active low-pass filter Q3. Audio from the filter is connected from Pin 9 to Audio PA transistor Q302. In Audio Amplifier module U310, an active high-pass filter is added in series with the low-pass filter to provide the required tone frequency roll-off.

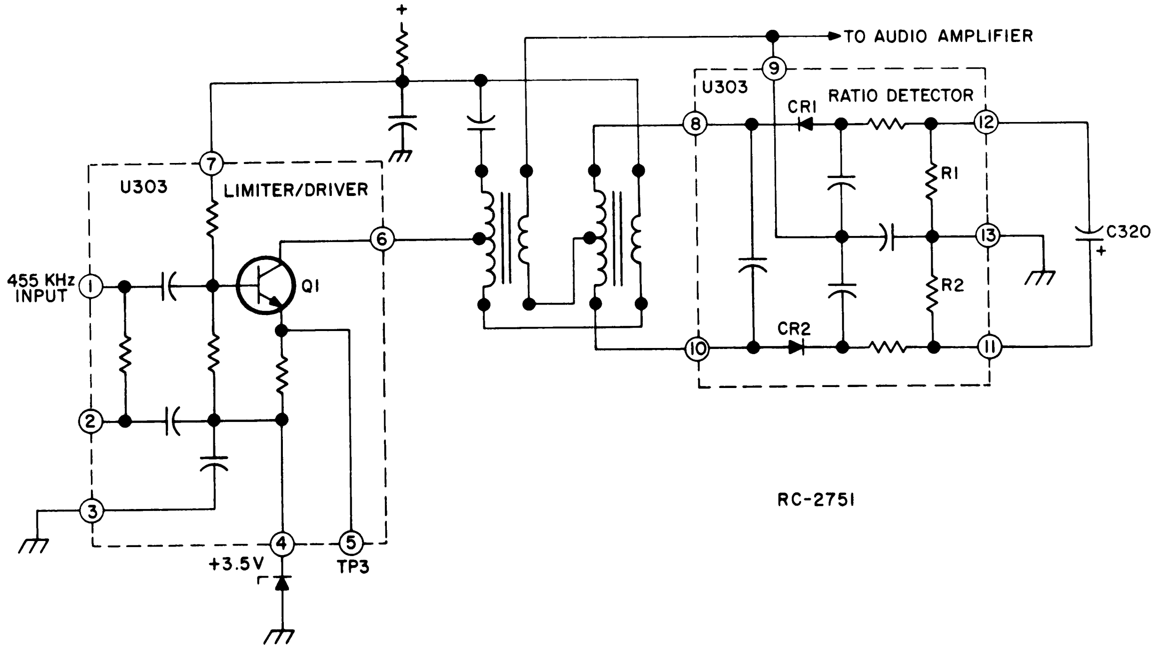


Figure 5 - Typical Driver/Limiter and Ratio Detector Circuit

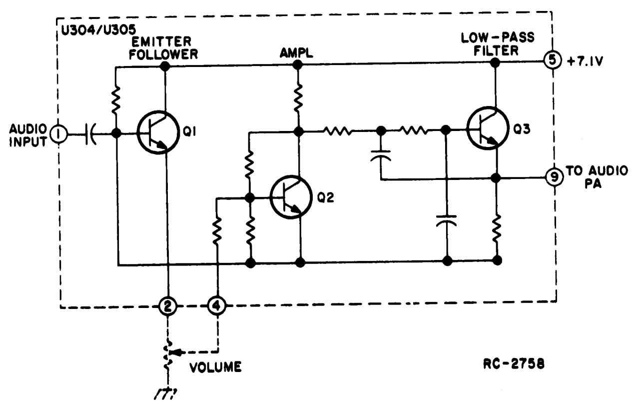


Figure 6 - Typical Audio Amplifier Circuit

AUDIO PA

When the receiver is quieted by a signal, audio from the active filter, in Audio Amplifier Module U304/U305, is coupled to the base of amplifier transistor Q302. The output of Q302 is direct coupled to the base of Driver transistor Q303. Q303 supplies drive for PA transistors Q304 and Q306. Q304 is driven direct from the collector of Q303. Drive from the collector of Q303 is applied to the base of bootstrap transistor Q305. The emitter of Q305 is direct coupled to Q306.

PA transistors Q304 and Q306 operate as complementary emitter-followers, providing a 500 milliwatt output into an 8-ohm load. Audio is coupled through capacitor C329 on the receiver board to speaker LS1.

SQUELCH

Noise from Audio Amplifier U304/U305 operates the squelch circuit. A typical squelch circuit is shown in Figure 7.

When no carrier is present in the receiver, the noise output of active high-pass filter Q1 is coupled to the base of noise amplifier Q2 through SQUELCH control R702. R702 controls the gain of the noise amplifier.

The output of noise amplifier Q2 is detected by diodes CR1 and CR2, and the resultant positive voltage turns off the PNP squelch switch Q3. In standard radios, the emitter of Q3 is connected to +7 Volts by means of a jumper from H1 to H2. When noise turns off Q3, its collector drops to ground potential. As the collector of Q3 is connected to the base of amplifier Q301 in the Audio PA module, turning off Q3 also turns off Q301, keeping the audio PA turned off.

When the receiver is quieted by a signal, squelch switch Q3 turns on. This applies +7 Volts to the base of amplifier Q1 in the Audio PA module, turning the Audio PA circuit on so that sound is heard at the speaker.

In tone decoder applications, the 7-Volt jumper from H1 to H2 is removed. The emitter of squelch switch Q3 is connected to 7.5 Volts by a DC switch on the decoder board.

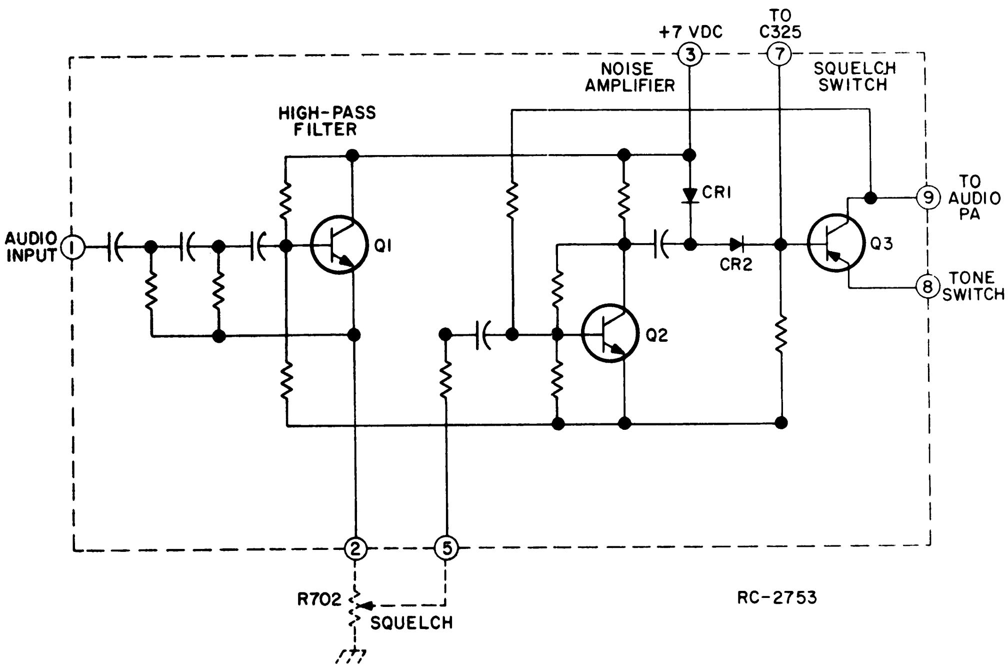


Figure 7 - Typical Squelch Circuit

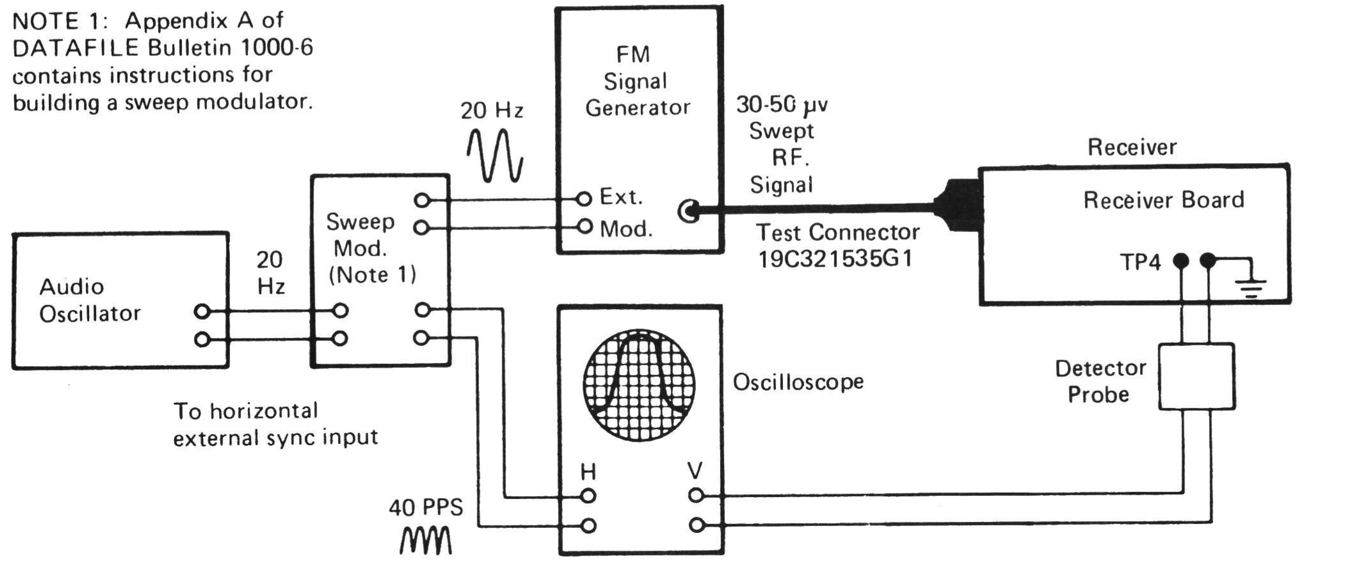


Figure 8 - Test Setup for 20-Hz Double-Trace Sweep Alignment

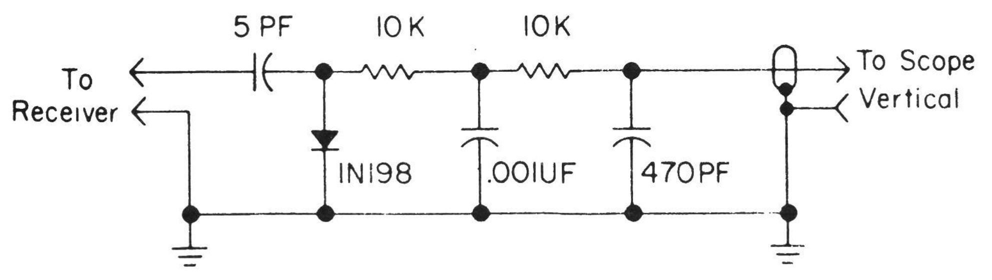
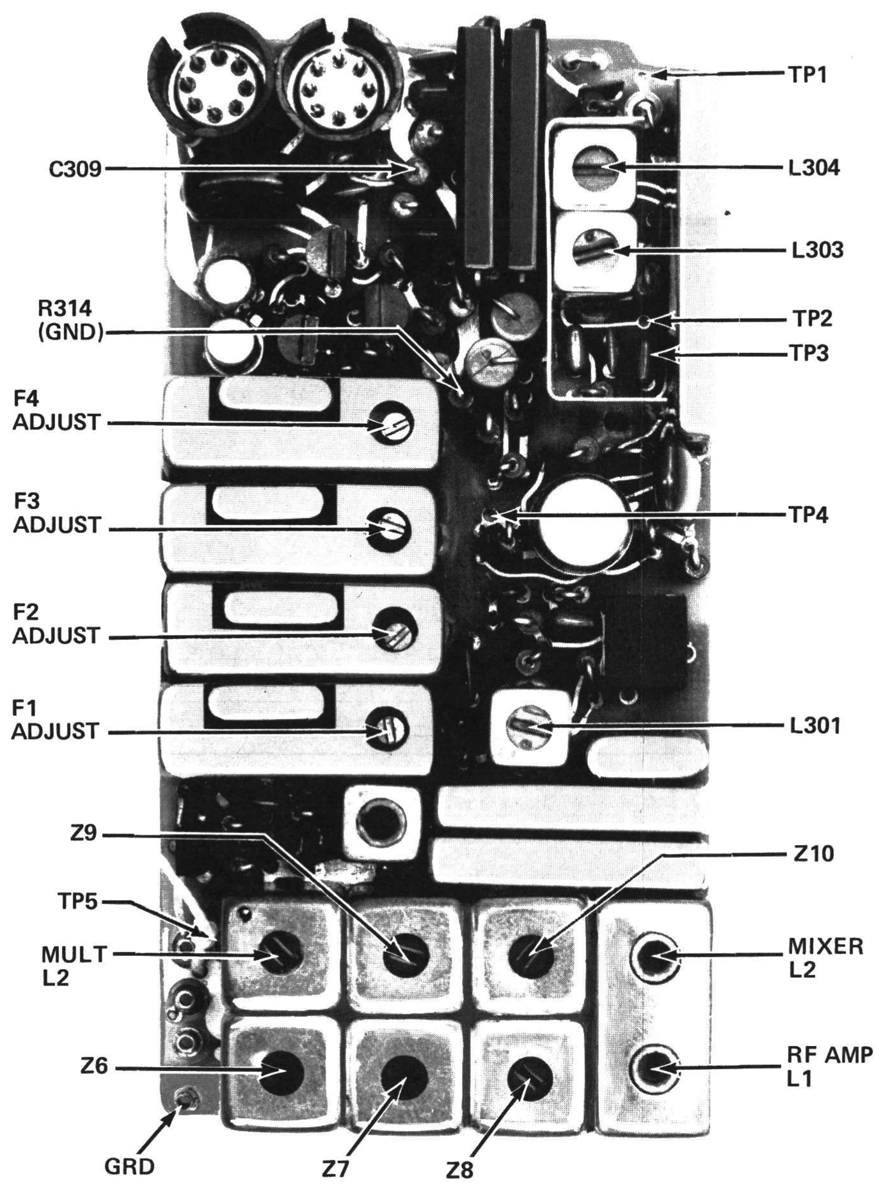


Figure 9 - Detector Probe for Sweep Alignment



RECEIVER ALIGNMENT

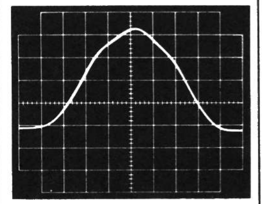
EQUIPMENT

1. A 20-MHz signal source (GE IF Generator Model 4EX9A10 or equivalent, a 455 kHz signal source (GE IF Generator Model 4EX7A10 or equivalent), and a 150.8-174 MHz source connected to the receiver through Receiver Test Connector 19C321535G1 inserted into antenna tube 19A127779G8.
2. GE Test Set Model 4EX3A10 or 4EX8K11 or voltmeter with equivalent sensitivity.
3. GE Test Amplifier Model 4EX16A10 and RF probe 19C311370G1, or equivalent RF voltmeter.
4. Distortion Analyzer or AC-VTVM.
5. Oscilloscope, 50 MV/DIV or better.

PRELIMINARY CHECKS AND ADJUSTMENTS

1. In multi-frequency receivers where the maximum frequency spacing is less than one MHz, align the receiver on the F1 channel. Where the frequency spacing is more than one MHz, align the receiver on the central frequency.
2. Set the slugs in Z6 thru Z10 to the bottom of the coil form for frequencies in the low end of the band. Set the slugs near the top of the coil form for frequencies near the high end of the band.
3. Set the slug in RF AMP L1 to the top of the coil form for frequencies in the low end of the band, and near the bottom of the coil form for frequencies near the high end of the band. Set mixer output coil L2 near the middle of the coil form.
4. Connect the negative lead of the DC Test Set TP1 and the positive lead to ground. Connect the Distortion Analyzer or AC-VTVM across the speaker leads.

ALIGNMENT PROCEDURE

STEP	TUNING CONTROL	PROCEDURE
		RATIO DETECTOR
1.	L303	Lightly couple a 455 kHz signal to U302-6. Adjust input for a slight increase at U303-12 (TP1). Tune L303 for a peak.
2.	L304	Adjust L304 to zero volts ±10 mV at TP2. Repeat steps 1 and 2. Disconnect 455 kHz generator.
		FRONT END MULTIPLIER
3.	MULT L2	Adjust L2 for maximum meter reading at TP5.
4.	Z8 and Z10	Adjust Z8 and then Z10 for slight change in meter reading at TP5.
		HIGH AND LOW IF
		The IF Circuits have been aligned at the factory and will normally require no further adjustment. Should an alignment become necessary, use the procedure outlined in Steps 5 and 6.
5.	See Procedure	Connect the scope, signal generator and detector as shown in Figures 9 and 10. Apply an on-frequency signal using the lowest possible input level to avoid limiting. Modulate the generator with 20 Hz at 10 to 16 kHz deviation. NOTE An on-frequency signal is easily determined by zero beating the channel signal with the 455 kHz marker generator signal. Loosely couple the 455 kHz generator to U301-4 and adjust the RF level of the RF signal generator to 20 dB quieting level.
6.	L2, L302, L301 	Tune L2 of mixer and L302 for the best response. Tune L301 for flatness. Retune L2, L302 and L301 for the best shape on scope as shown on scope wave form, keeping the signal below saturation.
		FRONT END
7.	Z6 thru Z8 and RF, Amp L1	Apply an on-frequency signal and adjust Z6, Z7, Z8 and L1 for best quieting sensitivity.
8.	MULT L2, Z9 and Z10	De-tune L2. Increase the on-frequency input signal and tune Z9 and Z10 for best quieting sensitivity. Now re-adjust L2 for maximum meter reading at TP5.
9.	L303, L304	Re-tune the ratio detector on noise. Peak L303 at TP1, zero TP2 by tuning L304. Detector idling should be zero volts ±10 mV.
		FREQUENCY ADJUSTMENT
10.		While applying an on-frequency signal, loosely couple a 455 kHz signal to the receiver. Adjust the oscillator trimmers for zero beat frequency between the two signals. Alternate Method: With no signal, measure and record the output of the ratio-detector with a DC-VTVM at TP2. Apply a strong on-frequency signal and tune the oscillator trimmers for the meter reading obtained at TP2.

ALIGNMENT PROCEDURE

150.8—174 MHz MVP PERSONAL RECEIVER
TYPE ER-71-A

TEST PROCEDURES

These Test Procedures are designed to help you to service a receiver that is operating --- but not properly. The problems encountered could be low power, poor sensitivity, distortion, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized.

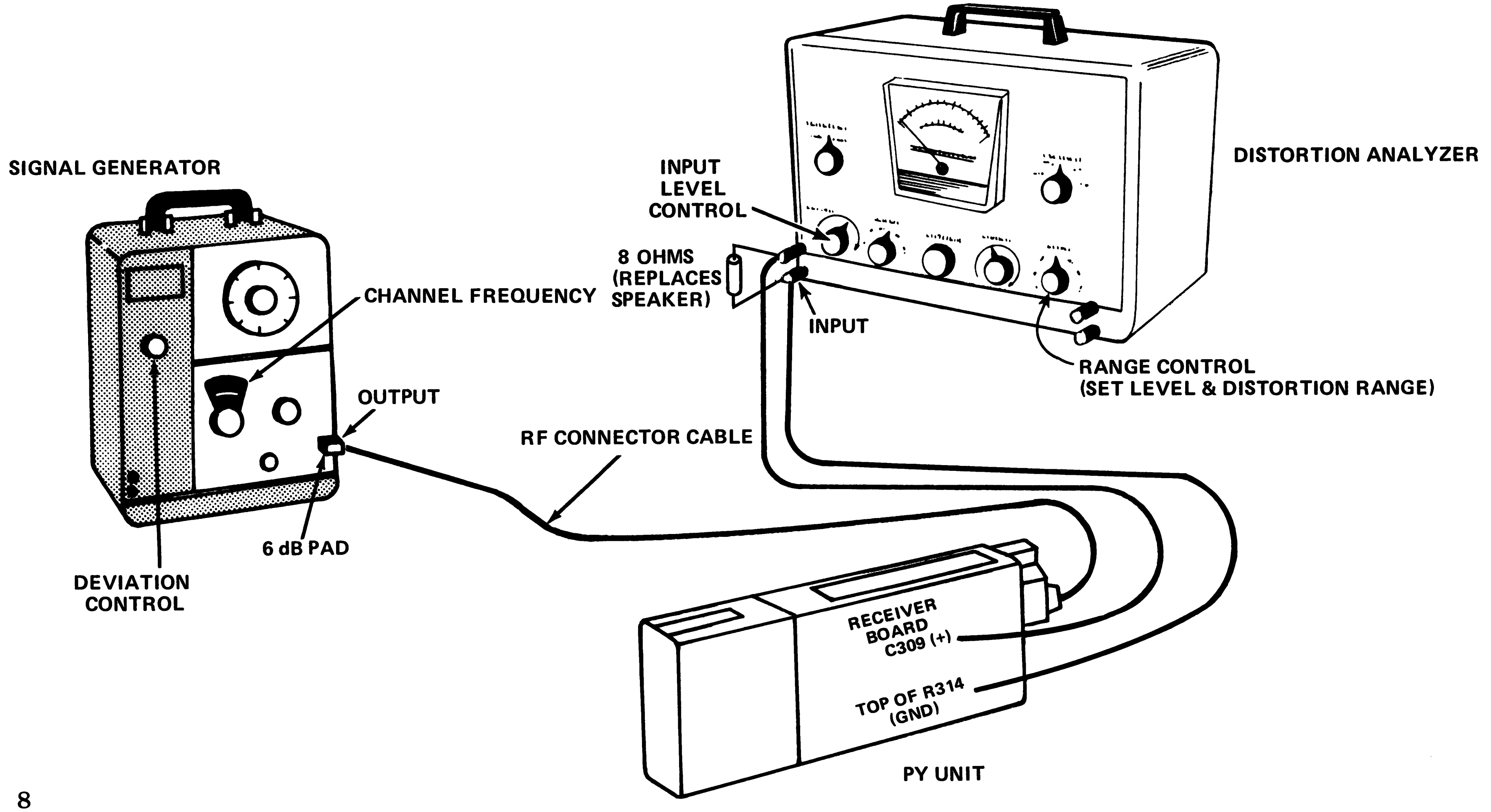
Once the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

TEST EQUIPMENT REQUIRED

- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-803
- 6-dB attenuation pad
- 8 ohm, 1 watt resistor
- RF Connector Cable 19C321535G1

PRELIMINARY ADJUSTMENTS

1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure. Refer to page 7 for connection points.
2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
3. Turn on all of the equipment and let it warm up for 20 minutes.



STEP 1

AUDIO POWER OUTPUT AND DISTORTION

TEST PROCEDURE

Measure Audio Power output as follows:

A. Connect a 1,000-microvolt test signal modulated by 1,000 hertz ±3.0 kHz deviation to the Antenna Connector.

B. Set the Volume Control for a 500 milliwatt output (2 volts RMS).

C. Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%-10% (5% is typical). If the receiver sensitivity is to be measured, leave all controls and equipment as they are.

SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than 0.5 watt, make the following checks:

D. Battery voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)

E. Audio Gain (Refer to Receiver Troubleshooting Procedure).

STEP 2

USABLE SENSITIVITY (12 dB SINAD)

TEST PROCEDURE

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

A. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.0 kHz deviation to the Antenna Connector.

B. Place the RANGE switch on the Distortion Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.)

C. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).

D. While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).

E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specification with an audio output of at least 250 milliwatts.

F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be performed.

SERVICE CHECK

If the sensitivity level is more than rated 12 dB SINAD, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

STEP 3

MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH)

TEST PROCEDURE

If STEPS 1 and 2 check out properly measure the bandwidth as follows:

A. Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.

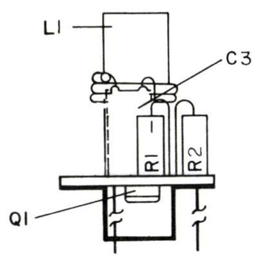
B. Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.

C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).

D. The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ±7 kHz (but less than ±9 kHz).

SERVICE CHECK

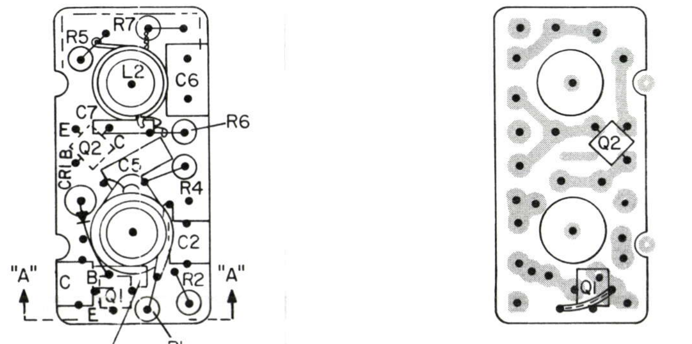
If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.



SECTION "A-A"

COMPONENT SIDE

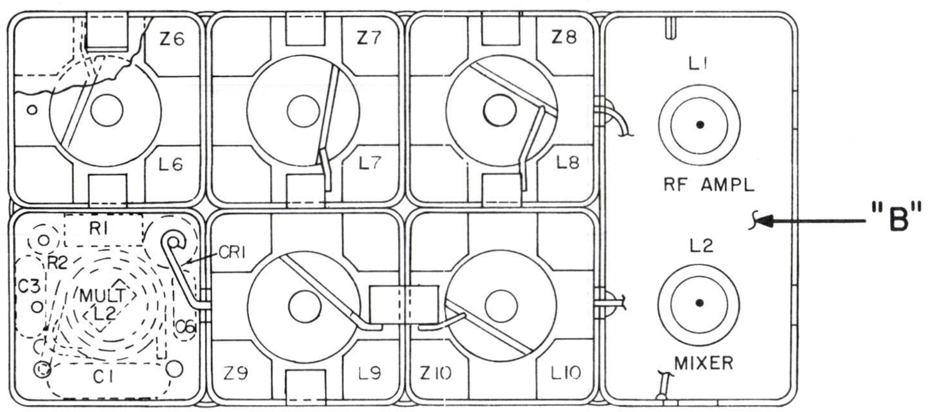
SOLDER SIDE



(19C320382, Sh. 2, Rev. 1)

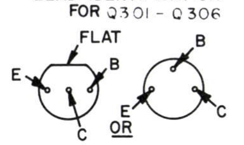
VIEW AT "B"

A305



BOTTOM VIEW

LEAD IDENTIFICATION FOR Q301 - Q306

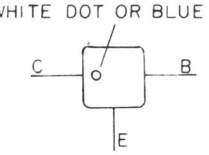


IN-LINE VIEW FROM LEAD END   TRIANGULAR

NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE, IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.

LEAD IDENTIFICATION FOR Q1 & Q2

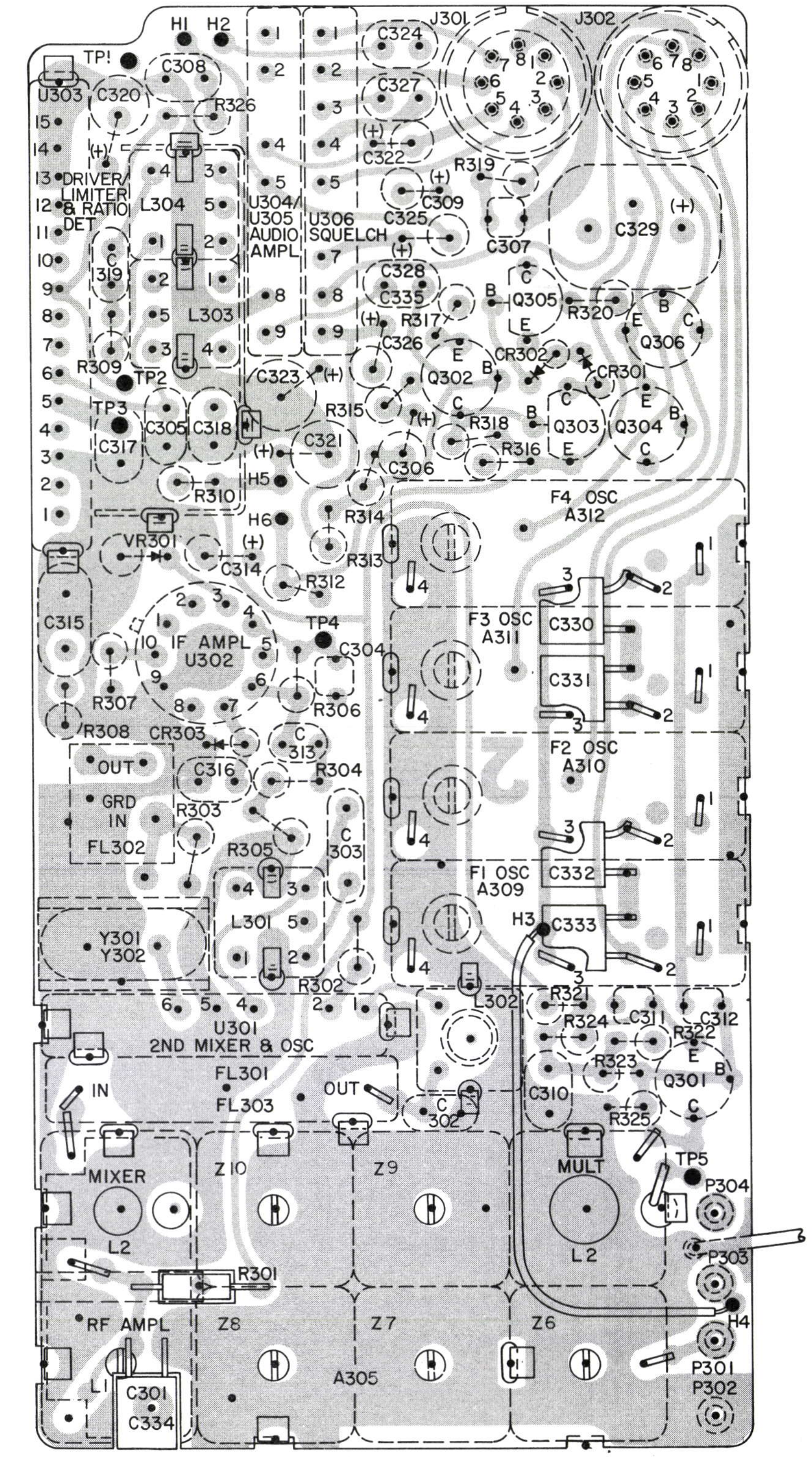
WHITE DOT OR BLUE PAINT



COMPONENT SIDE

(19D423526, Rev. 5)
(19D423092, Sh. 2, Rev. 2)
(19D423092, Sh. 3, Rev. 1)

SOLDER SIDE



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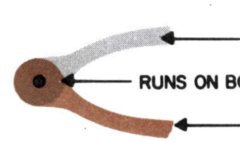
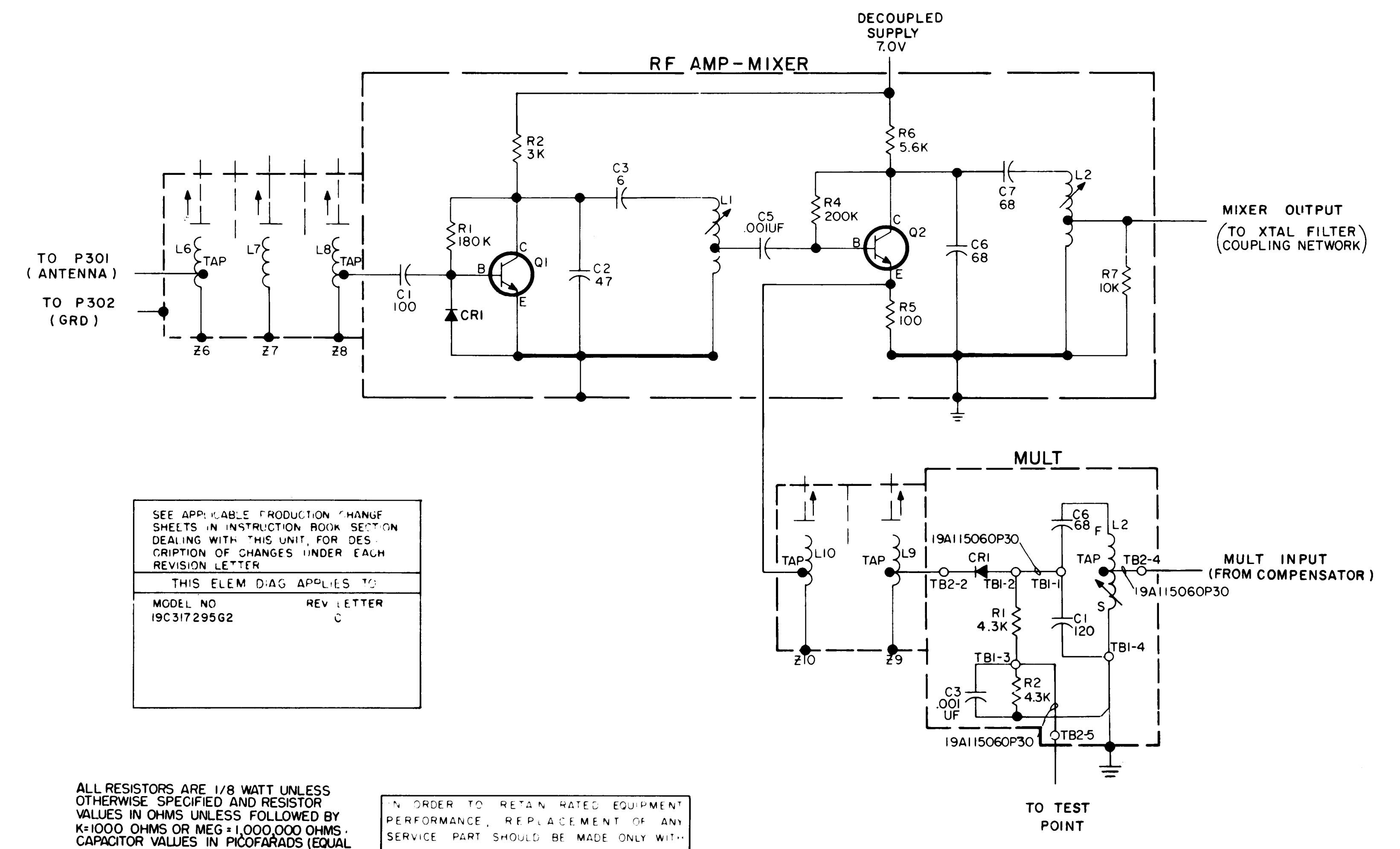
OUTLINE DIAGRAM



150.8—174 MHz MVP PERSONAL RECEIVER
TYPE ER-71-A



SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DESCRIPTION OF CHANGES UNDER EACH REVISION LETTER	
THIS ELEM DIAG APPLIES TO	
MODEL NO	REV LETTER
19C317295G2	C

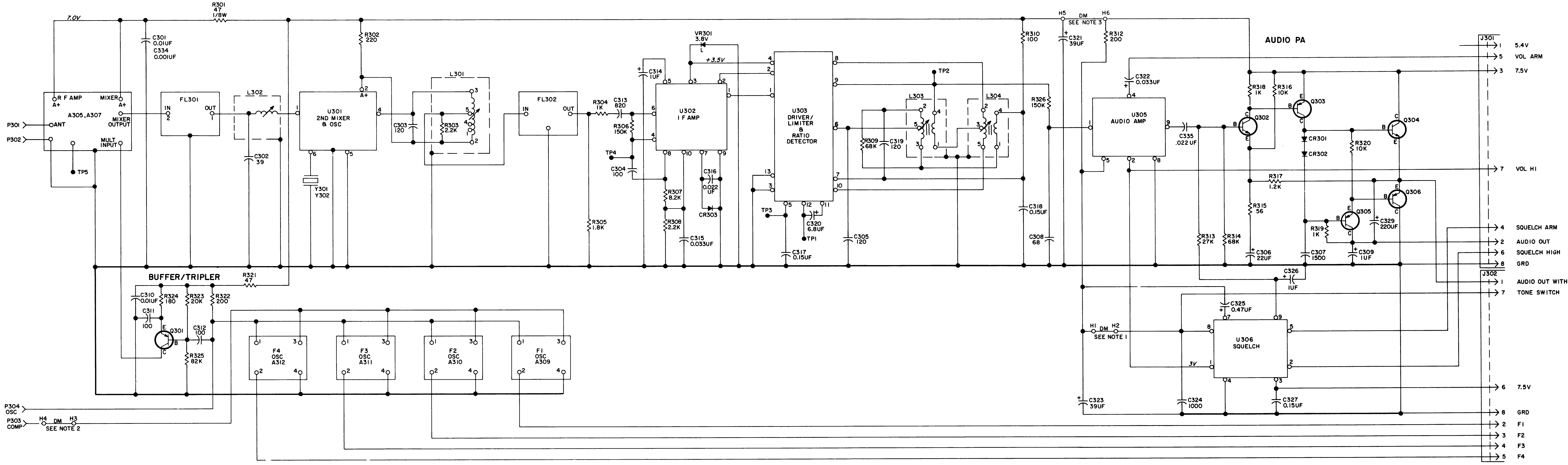
ALL RESISTORS ARE 1/8 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

(19C320888, Rev. 4)

SCHEMATIC DIAGRAM

150.8—174 MHz RECEIVER FRONT END
TYPE ER-71-A



ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

NOTES:
1. JUMPER PRESENT IN G1 AND G3 ONLY.
2. JUMPER PRESENT IN G3 AND G4 ONLY.
3. JUMPER PRESENT IN ALL GROUPS

SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DESCRIPTION OF CHANGES UNDER EACH REVISION LETTER.	
THIS ELEM DIAG APPLIES TO	
MODEL NO	REV LETTER
PL19D423091G1	B
PL19D423091G2	B
PL19D423091G3	B
PL19D423091G4	B

(19R622145, Rev. 5)

SCHEMATIC DIAGRAM

150.8—174 MHz MVP PERSONAL RECEIVER
TYPE ER-71-A

PARTS LIST

LBI-4889A

150.8-174 MHz RECEIVER ER-71-A
19D423091G1 STANDARD
19D423091G2 CHANNEL GUARD

SYMBOL	GE PART NO.	DESCRIPTION
A305		FRONT END ASSEMBLY 19C317295G2
A1*		RF AMPLIFIER 19C327300G1 (Added by REV C)
		- - - - - - - - - - - CAPACITORS - - - - - - - - - -
C1	19A116114P11064	Ceramic: 100 pf ±10%, 100 VDCW; temp coef -4200 PPM.
C2	19A116114P8053	Ceramic: 47 pf ±5%, 100 VDCW; temp coef -1500 PPM.
C3	19A116114P2020	Ceramic: 6 pf ±5%, 100 VDCW; temp coef -80 PPM.
C5	5495323P12	Ceramic: .001 µf +100% -20%, 75 VDCW.
C6 and C7	19A116114P4059	Ceramic: 68 pf ±5%, 100 VDCW; temp coef -220 PPM.
		- - - - - - - - DIODES AND RECTIFIERS - - - - - - -
CR1	19A116052P1	Silicon.
		- - - - - - - - - - - INDUCTORS - - - - - - - - - -
L1	19B216950G1	Coil.
L2	19B216948G1	Coil.
		- - - - - - - - - - - TRANSISTORS - - - - - - - -
Q1 and Q2	19A116159P1	Silicon, NPN.
		- - - - - - - - - - - RESISTORS - - - - - - - - - -
R1	3R151P184J	Composition: 0.18 megohm ±5%, 1/8 w.
R2	3R151P302J	Composition: 3000 ohms ±5%, 1/8 w.
R4	3R151P204J	Composition: 0.20 megohm ±5%, 1/8 w.
R5	3R151P101J	Composition: 100 ohms ±5%, 1/8 w.
R6	3R151P562J	Composition: 5600 ohms ±5%, 1/8 w.
R7	3R151P103J	Composition: 10,000 ohms ±5%, 1/8 w.
A1*		RF AMPLIFIER 19C317445G1 (Deleted by REV C)
		- - - - - - - - - - - CAPACITORS - - - - - - - - - -
C1	19A116114P11064	Ceramic: 100 pf ±10%, 100 VDCW; temp coef -4200 PPM.
C2	19A116114P8053	Ceramic: 47 pf ±5%, 100 VDCW; temp coef -1500 PPM.
C3	19A116114P2020	Ceramic: 6 pf ±5%, 100 VDCW; temp coef -80 PPM.
C5	5495323P12	Ceramic: .001 µf +100% -20%, 75 VDCW.
C6 and C7	19A116114P4059	Ceramic: 68 pf ±5%, 100 VDCW; temp coef -220 PPM.
		- - - - - - - - DIODES AND RECTIFIERS - - - - - - -
CR1	19A116052P1	Silicon.
		- - - - - - - - - - - INDUCTORS - - - - - - - - - -
L1	19B216950G1	Coil.
L2	19B216948G1	Coil.
		- - - - - - - - - - - TRANSISTORS - - - - - - - -
Q1 and Q2	19A116159P1	Silicon, NPN.

SYMBOL	GE PART NO.	DESCRIPTION
		- - - - - - - - - - - RESISTORS - - - - - - - - - -
R1	3R151P184J	Composition: 0.18 megohm ±5%, 1/8 w.
R2	3R151P302J	Composition: 3000 ohms ±5%, 1/8 w.
R4	3R151P204J	Composition: 0.20 megohm ±5%, 1/8 w.
R5	3R151P101J	Composition: 100 ohms ±5%, 1/8 w.
R6	3R151P562J	Composition: 5600 ohms ±5%, 1/8 w.
R7	3R151P103J	Composition: 10,000 ohms ±5%, 1/8 w.
A4		MULTIPLIER 19C311873G5
		- - - - - - - - - - - CAPACITORS - - - - - - - - - -
C1	19A116114P7068	Ceramic: 120 pf ±5%, 100 VDCW; temp coef -750 PPM.
C3	5495323P12	Ceramic: .001 µf +100% -20%, 75 VDCW.
C6	19A116114P4059	Ceramic: 68 pf ±5%, 100 VDCW; temp coef -220 PPM.
		- - - - - - - - DIODES AND RECTIFIERS - - - - - - -
CR1	19A116081P1	Silicon.
		- - - - - - - - - - - INDUCTORS - - - - - - - - -
L2	19B216296P2	Coil. Includes:
	19B200495P5	Tuning slug.
		- - - - - - - - - - - RESISTORS - - - - - - - - - -
R1	3R151P432J	Composition: 4300 ohms ±5%, 1/8 w.
R9	3R151P432J	Composition: 4300 ohms ±5%, 1/8 w.
		- - - - - - - - - - - INDUCTORS - - - - - - - - - -
L6	19B216441G2	Helical resonator. (Part of Z6). Includes:
	19C311727P1	Tuning slug.
L7	19B216441G3	Helical resonator. (Part of Z7). Includes:
	19C311727P1	Tuning slug.
L8	19B216441G12	Helical resonator. (Part of Z8). Includes:
	19C311727P1	Tuning slug.
L9 and L10	19B216441G4	Helical resonator. (Part of Z9, Z10). Includes:
	19C311727P1	Tuning slug.
		- - - - - - - - HELICAL RESONATORS - - - - - - - -
Z6		Consists of L6 and 19D413132P16 can.
Z7		Consists of L7 and 19D413132P3 can.
Z8		Consists of L8 and 19D413132P17 can.
Z9		Consists of L9 and 19D413132P19 can.
Z10		Consists of L10 and 19D413132P20 can.
		- - - - - - - - - - OSCILLATORS - - - - - - - - -
A309 thru A312		NOTE: When reordering, give GE Part Number and specify exact frequency needed.
	4EG36A10	Oscillator Module. 150.8-174 MHz. $Fx = \frac{Fo - 20}{9}$
		- - - - - - - - - - - CAPACITORS - - - - - - - - - -
C301	19A116192P1	Ceramic: 0.01 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.
C302	19A116114P2050	Ceramic: 39 pf ±5%, 100 VDCW; temp coef -80 PPM.
C303	19A116114P5068	Ceramic: 120 pf ±5%, 100 VDCW; temp coef -330 PPM.
C304	19A116114P13065	Ceramic: 100 pf ±5%, 100 VDCW; temp coef -5600 PPM.
C305	19A116288P9	Ceramic: 120 pf ±5%, 100 VDCW; sim to Erie 8121-A100-U2J-121J.

SYMBOL	GE PART NO.	DESCRIPTION
C306	5491674P35	Tantalum: 22 µf ±20%, 4 VDCW; sim to Sprague Type 162D.
C307	19A116192P10	Ceramic: 1500 pf ±20%, 50 VDCW; sim to Erie 8121-050-W5R.
C308	19A116114P6059	Ceramic: 68 pf ±5%, 100 VDCW; temp coef -470 PPM.
C309	5491674P28	Tantalum: 1.0 µf ±20%, 25 VDCW; sim to Sprague Type 162D.
C310	19A116192P1	Ceramic: 0.01 µf ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.
C311 and C312	19A116114P13065	Ceramic: 100 pf ±5%, 100 VDCW; temp coef -5600 PPM.
C313	19A116192P9	Ceramic: 820 pf ±20%, 50 VDCW; sim to Erie 8111-050-W5R.
C314	5491674P28	Tantalum: 1.0 µf ±20%, 25 VDCW; sim to Sprague Type 162D.
C315	19A116080P104	Polyester: 0.033 µf ±10%, 50 VDCW.
C316	19A116244P2	Ceramic: 0.022 µf ±20%, 50 VDCW.
C317 and C318	19A116244P4	Ceramic: 0.15 µf ±20%, 50 VDCW.
C319	19A116114P7068	Ceramic: 120 pf ±5%, 100 VDCW; temp coef -750 PPM.
C320	5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.
C321	5491674P30	Tantalum: 39 µf ±20%, 10 VDCW; sim to Sprague Type 162D.
C322	5491674P31	Tantalum: .033 µf ±20%, 35 VDCW; sim to Sprague Type 162D.
C323	5491674P30	Tantalum: 39 µf ±20%, 10 VDCW; sim to Sprague Type 162D.
C324	19A116192P13	Ceramic: 1000 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W5R.
C325	5491674P27	Tantalum: .47 µf ±20%, 35 VDCW; sim to Sprague Type 162D.
C326	5491674P28	Tantalum: 1.0 µf ±20%, 25 VDCW; sim to Sprague Type 162D.
C327	19A116244P4	Ceramic: 0.15 µf ±20%, 50 VDCW.
C328	19A116244P5	Ceramic: 0.1 µf ±20%, 50 VDCW.
C329	19A116178P7	Tantalum: 220 µf ±20%, 6 VDCW.
C330* and C333*	19A116192P13	Ceramic: 1000 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W5R. Deleted by REV B.
		- - - - - - - - DIODES AND RECTIFIERS - - - - - -
CR301 thru CR303	19A115250P1	Silicon.
		- - - - - - - - - - - - FILTERS - - - - - - - - - -
FL301	19C304824G1	Bandpass: 20 MHz.
FL302	19A134199P1	Bandpass: 20 KHz at 6 db, 40 KHz at 40 db.
		- - - - - - - - JACKS AND RECEPTACLES - - - - - - -
J301 and J302	19A116122P1	Terminal, feed-thru.
		- - - - - - - - - - - INDUCTORS - - - - - - - - - -
L301	19A116308P3	IF Transformer: sim to Toko, Inc. LMN-6586Y.
L302	19B219864G4	Coil. Includes:
	19B209436P1	Tuning slug.
L303	19A116308P1	IF Transformer: sim to Toko, Inc. LSN4816VE2.
L304	19A116308P2	IF Transformer: sim to Toko, Inc. LSN4817YM2.
		- - - - - - - - - - - - PLUGS - - - - - - - - - - -
P301 thru P304	19A115834P4	Contact, electrical: sim to AMP 2-332070-9.
		- - - - - - - - - - - TRANSISTORS - - - - - - - -
Q301	19A116223P1	Silicon, PNP; sim to Type 2N3640.
Q302	19A116774P1	Silicon, NPN; sim to Type 2N5210.

SYMBOL	GE PART NO.	DESCRIPTION
Q303	19A115852P1	Silicon, PNP; sim to Type 2N3906.
Q304	19A115720P1	Silicon, NPN; sim to Type 2N2222.
Q305	19A115852P1	Silicon, PNP; sim to Type 2N3906.
Q306	19A134165P1	Silicon, PNP; sim to Type 2N2906A.
		- - - - - - - - - - - RESISTORS - - - - - - - - - -
R301	3R151P470J	Composition: 47 ohms ±5%, 1/8 w.
R302	3R152P221J	Composition: 220 ohms ±5%, 1/4 w.
R303	3R152P222J	Composition: 2200 ohms ±5%, 1/4 w.
R304	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.
R305	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.
R306	3R152P154J	Composition: 0.15 megohm ±5%, 1/4 w.
R307	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.
R308	3R152P222J	Composition: 2200 ohms ±5%, 1/4 w.
R309	3R152P683J	Composition: 68,000 ohms ±5%, 1/4 w.
R310	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.
R312	3R152P201J	Composition: 200 ohms ±5%, 1/4 w.
R313	3R152P273J	Composition: 27,000 ohms ±5%, 1/4 w.
R314	3R152P683J	Composition: 68,000 ohms ±5%, 1/4 w.
R315	3R152P560J	Composition: 56 ohms ±5%, 1/4 w.
R316	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.
R317	3R152P122J	Composition: 1200 ohms ±5%, 1/4 w.
R318 and R319	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.
R320	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.
R321	3R152P470J	Composition: 47 ohms ±5%, 1/4 w.
R322	3R152P221J	Composition: 220 ohms ±5%, 1/4 w.
R323	3R152P203J	Composition: 20,000 ohms ±5%, 1/4 w.
R324	3R152P181J	Composition: 180 ohms ±5%, 1/4 w.
R325	3R152P823J	Composition: 82,000 ohms ±5%, 1/4 w.
R326	3R152P154J	Composition: 0.15 megohm ±5%, 1/4 w.
		- - - - - - - - - INTEGRATED CIRCUITS - - - - - -
U301	19C321359G1	2nd Oscillator, Mixer.
U302	19A116208P2	Monolithic, linear.
U303	19D423113G1	Detector.
U304	19C311878G2	Audio Amplifier.
U305	19C311995G2	Audio Amplifier. (Includes Tone Filter).
U306	19C311880G4	Squelch.
		- - - - - - - - - VOLTAGE REGULATORS - - - - - -
VR301	4036887P3	Silicon, Zener.
		- - - - - - - - - - - - CRYSTALS - - - - - - - - - -
Y301	19B206357P4	Quartz: freq range 12-20 MHz, temp range -30°C to +85°C.
		- - - - - - - - - - MISCELLANEOUS - - - - - - - -
	19B216316P1	Insulator. (Used with J301, J302).
	19A116120P3	Can. (Used with L302).
	19B226696P1	Shield. (Located at L303, L304).
	19B219801P2	Shield. (Located over A4 and L6-L10).
	19B200497P5	Tuning slug. (Used with Multiplier-A4).

SYMBOL	GE PART NO.	DESCRIPTION
		ASSOCIATED ASSEMBLIES
		CONNECTOR KIT 19C321535G1
		- - - - - - - - - - - - CAPACITORS - - - - - - - - - -
C1	19A116114P1	Ceramic: 1 pf ±10%, 100 VDCW; temp coef 0 PPM. (Part of W1).
C2	19A116114P1	Ceramic: 1 pf ±10%, 100 VDCW; temp coef 0 PPM.
		- - - - - - - - JACKS AND RECEPTACLES - - - - - - -
J1	7776570P17	Receptacle, bulkhead: coaxial, 500 v peak. Military Type MS35179 REV.B-1094/U.
		- - - - - - - - - - - - CABLES - - - - - - - - - - -
W1	19B226852G1	Cable assembly. Includes C1.

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

PRODUCTION CHANGES

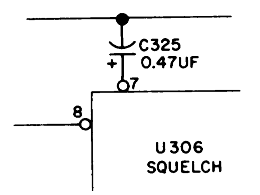
Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV A & B - Receiver Front End 19C317295G2
Incorporated into initial shipment.

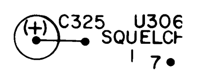
REV. C - To improve ease of assembly, troubleshooting and repair. Changed RF Amplifier A1.

REV. A - Receiver Board 19D423091G1 & G2
To improve receiver attack time with Channel Guard Option. Changed connection of C325.

Schematic Diagram was:



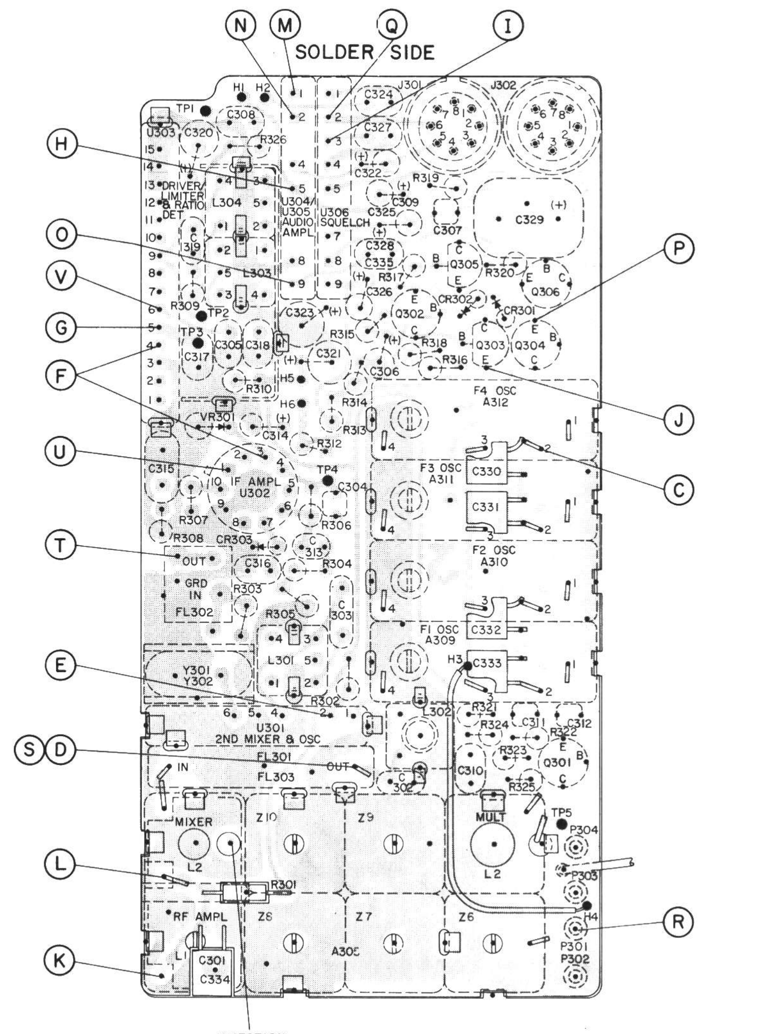
Outline Diagram was:



REV. B - To improve design.
Deleted C330 through C333.

QUICK CHECKS

SYMPTON	PROCEDURE
No Audio	1. Check audio waveform at the top of the Volume Control (see Step 2). 2. If audio is present, check voltage readings of Audio and Squelch modules (see Schematic Diagram). 3. If audio is not present, check gain and current readings of Front End and IF modules (see Steps 1 & 3).
Poor Sensitivity	1. Measure the gain of the Mixer stage (see Step 3). If low, measure the gain of the RF amplifier and IF modules.
Improper Squelch Operation	1. Check the noise waveform at the input to the Squelch module and at Squelch Control high (see Step 2). 2. Measure the DC voltages for the Squelch module (squelched and unsquelched).



INJECTION VOLTAGE TEST POINT

(RC-2781)
(19D423526, Rev. 5)
(19D423092, Sh. 2, Rev. 2)

STEP 3 - RF GAIN CHECKS

EQUIPMENT REQUIRED:

1. RF probe and Test Amplifier Model 4EX16A10 connected to GE Test Set Model 4EX3A11, or an RF voltmeter.
2. A signal generator (M-800 or equivalent) connected to P301 (High) and P302 (Low).

PROCEDURE FOR MIXER AND 1ST IF:

1. Disable 2nd Oscillator by shorting Y301 with a .01 μf capacitor.
2. Switch the Test Set to the Test 1 position and the Test Amplifier to the X50 position.
3. Connect the RF probe across the input (R) as shown on the diagram. Increase the signal generator output to obtain a reference reading on Test Set 4EX3A11. Note the Test Set reading and the dB reading on the generator (dB1).
4. Connect the RF probe to the output (S) as shown on the diagram. Decrease the generator output until the Test Set reference reading in Step 3 is obtained. Note the dB reading on the generator (dB2).
5. Subtract the dB1 reading from the dB2 reading and check the results with the typical gains shown on the diagram.

   Example:
   35 dB (dB2)
   -15 dB (dB1)
   20 dB gain

6. Remove .01 μf shorting capacitor.

PROCEDURE FOR 2ND MIXER:

1. With no signal in, connect the RF probe to the output of the 2nd IF filter FL302 at (T). Increase the signal generator output until the Test Set reading increases by approximately 0.2 volt. Note Test Set and signal generator reading (dB2).
2. Connect the probe to the input of the 2nd Mixer module at (S) Increase the signal generator until the Test Set reference reading is obtained, and note the dB reading (dB1).
3. Now substract dB2 from dB1 to obtain the gain of the 2nd Mixer.

PROCEDURE FOR 2ND IF AMPLIFIER:

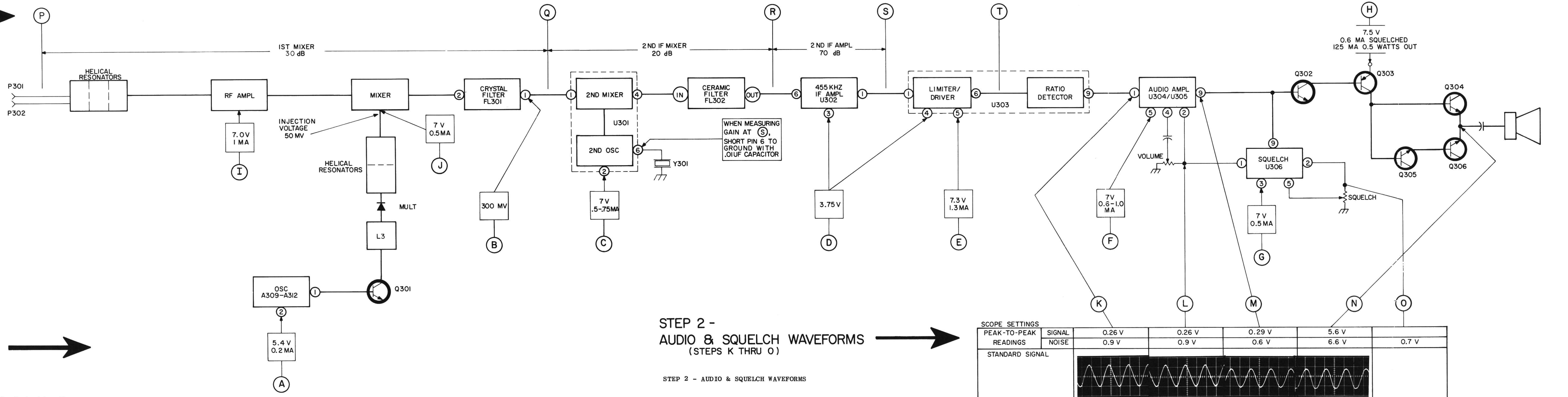
1. Connect the RF probe across the input of the 2nd IF Amplifier at (T). Increase the signal generator output to obtain a reference level on Test Set 4EX3A11. Note the Test Set reading and the dB reading on the generator (dB1).
2. Connect the RF probe to the output at (U) as shown on the diagram. Decrease the generator output until the Test Set reference reading in Step 1 is obtained. Note the dB reading on the generator (dB2).
3. Subtract the dB1 reading from the dB2 reading and check the results with the typical gains on the diagram.

LIMITER CHECK:

The limiter module limits on noise so that the gain of the circuit cannot be measured. The following procedure provides a check to determine if the module is limiting.

1. Switch the Test Amplifier to the X1 position and the Test Set to the Test 1 position. Then connect the RF probe to the output of the Limiter module (V) and check for a reading of approximately 0.25 VDC.
2. Increase the signal generator output. There should be no appreciable increase in the limiter output meter reading.

STEP 3-RF GAIN CHECKS
(STEPS P THRU T)



STEP 1- MODULE CURRENT CHECKS
(STEPS A THRU K)

STEP 1 - MODULE CURRENT CHECKS

These current readings provide a method of checking the operation of each Integrated Circuit module using a milliammeter (Triplett 630 or equivalent).

1. Unsolder the + lead as shown in the Diagram of the module to be checked.
2. Connect the milliammeter in series with the + lead, and check for the indicated current drain and supply voltage. No current drain indicates that the module should be replaced.

CAUTION

When checking the current of Audio PA module A311, do not short Pin 4 to ground or to + (Pin 5). To do so will destroy the Audio PA module.

STEP 2 - AUDIO & SQUELCH WAVEFORMS
(STEPS K THRU O)

STEP 2 - AUDIO & SQUELCH WAVEFORMS

EQUIPMENT REQUIRED:

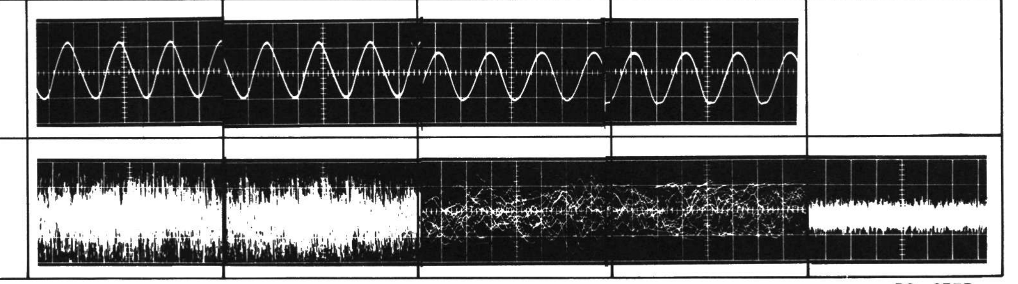
- Oscilloscope connected between the points shown and ground.
- Signal Generator (Measurements M-800 or equivalent).

PRELIMINARY STEPS:

1. Apply a standard signal to P301. A standard signal is 1000 microvolts on the receiver frequency modulated by one kHz with 3.0-kHz deviation.
2. Set the Volume control for 0.5-watt output.

SCOPE SETTINGS

PEAK-TO-PEAK READINGS		K	L	M	N	O
	SIGNAL	0.26 V	0.26 V	0.29 V	5.6 V	
	NOISE	0.9 V	0.9 V	0.6 V	6.6 V	0.7 V
STANDARD SIGNAL						
NOISE WAVEFORM						



RC-2777

TROUBLESHOOTING PROCEDURE

150.8—174 MHz MVP PERSONAL RECEIVER
TYPE ER-71-A

ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

1. GE Part Number for component
2. Description of part
3. Model number of equipment
4. Revision letter stamped on unit

MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY • LYNCHBURG, VIRGINIA 24502

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